



# ZT3150

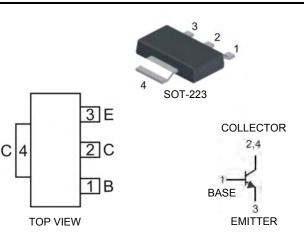
#### NPN SURFACE MOUNT TRANSISTOR

#### Features

- **Epitaxial Planar Die Construction** •
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

### Mechanical Data

- Case: SOT-223 •
- Case Material: Molded Plastic, "Green" Molding Compound. • UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams (approximate)



Schematic and Pin Configuration

#### **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	V <sub>CBO</sub>	50	V	
Collector-Emitter Voltage	V <sub>CEO</sub>	25	V	
Emitter-Base Voltage	V <sub>EBO</sub>	7.0	V	
Collector Current	lc	5.0	A	
Base Current	IB	1.0	А	
Power Dissipation	P <sub>D</sub>	1 (Note 3) 2 (Note 4)	W	
Thermal Resistance, Junction-to-Ambient	R <sub>0JA</sub>	125 (Note 3) 62.5 (Note 4)	°C/W	
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-65 to +150	°C	

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

3. Device mounted on FR-4 PCB, pad layout as shown on page 4.

Device mounted on Polyimide PCB with a copper area of 1.8cm<sup>2</sup> 4.



# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	25		_	V	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$
Collector Cutoff Current	I <sub>CBO</sub>	_		1.0	μA	$V_{CB} = 50V, I_E = 0$
Emitter Cutoff Current	I <sub>EBO</sub>	_		1.0	μA	$V_{EB} = 7.0V, I_{C} = 0$
ON CHARACTERISTICS						
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_		0.35 0.50	V V	$I_{C} = 3.0A, I_{B} = 150mA^{*}$ $I_{C} = 4.0A, I_{B} = 200mA^{*}$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_		1.10 1.40	V V	I <sub>C</sub> = 3.0A, I <sub>B</sub> = 150mA* I <sub>C</sub> = 4.0A, I <sub>B</sub> = 200mA*
DC Current Gain	h <sub>FE</sub>	250 150 50		500 —	_	$ \begin{array}{ll} I_{\rm C} = 500 \text{mA}, & V_{\rm CE} = 2.0 \text{V}^{\star} \\ I_{\rm C} = 2.0 \text{A}, & V_{\rm CE} = 2.0 \text{V}^{\star} \\ I_{\rm C} = 5.0 \text{A}, & V_{\rm CE} = 2.0 \text{V}^{\star} \end{array} $
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f <sub>T</sub>		150		MHz	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 6.0V, f = 200MHz
Output Capacitance	C <sub>obo</sub>	_		50	pF	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz

\* Measured under pulsed conditions. Pulse width = 300 $\mu$ s. Duty cycle  ${\leq}2\%$ 

# Typical Characteristics @T<sub>amb</sub> = 25°C unless otherwise specified

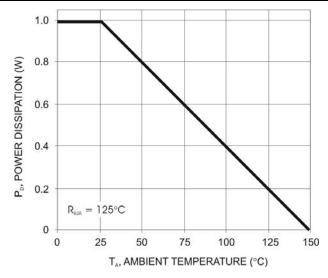


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

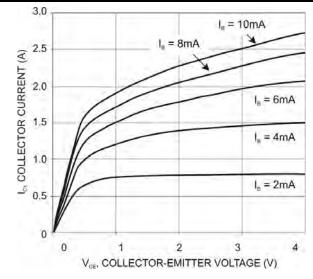
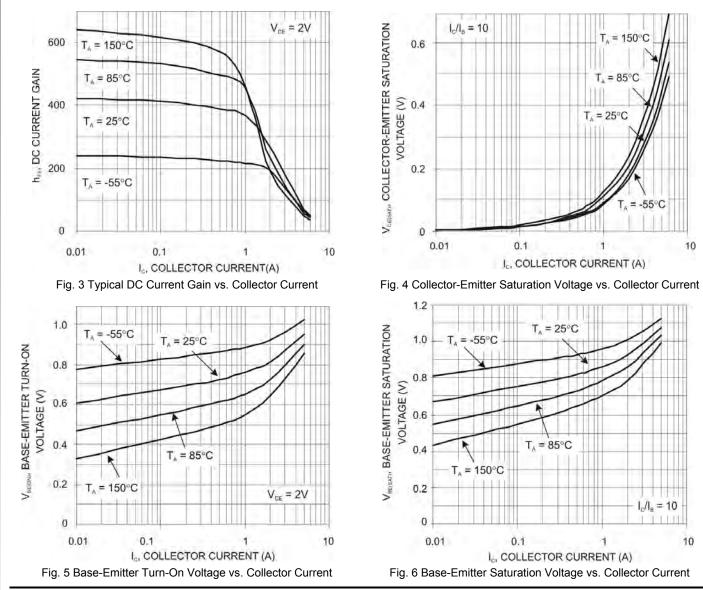


Fig. 2 Collector Current vs. Collector Emitter-Voltage

Notes: 3. Device mounted on FR-4 PCB, pad layout as shown on page 4.



NEW PRODUCT

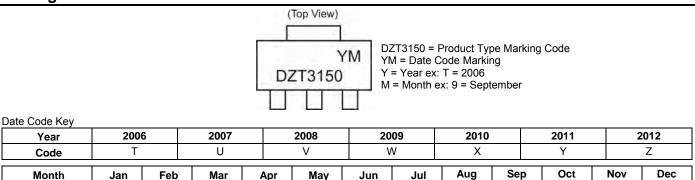


#### Ordering Information (Note 5)

Device	Packaging	Shipping
DZT3150-13	SOT-223	2500/Tape & Reel

Notes: 5. Packaging Details as shown on page 4, or go to our website at http://www.diodes.com/ap2007.pdf.

#### **Marking Information**



Code

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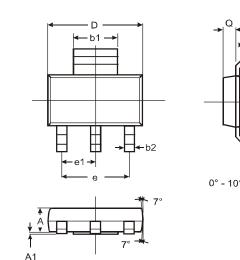
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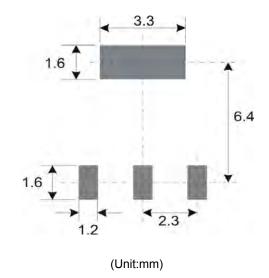


#### Package Outline Dimensions



SOT-223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_	_	4.60		
e1	_	_	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

## Suggested Pad Layout: (Based on IPC-SM-782)



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F1

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